

40V N-Channel NexFET™ Power MOSFETs

Check for Samples: [CSD18503Q5A](#)

FEATURES

- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- Logic Level
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

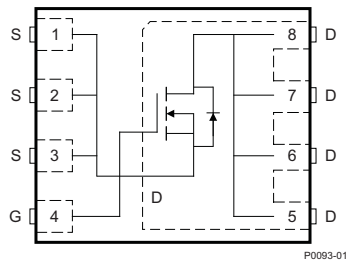
APPLICATIONS

- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- Battery Motor Control

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.

Figure 1. Top View



PRODUCT SUMMARY

Typical Values at 25°C unless otherwise stated		TYPICAL VALUE	UNIT
V _{DS}	Drain to Source Voltage	40	V
Q _g	Gate Charge Total (4.5V)	13	nC
Q _{gd}	Gate Charge Gate to Drain	4.3	nC
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 4.5V	4.7 mΩ
		V _{GS} = 10V	3.4 mΩ
V _{GS(th)}	Threshold Voltage	1.8	V

ORDERING INFORMATION

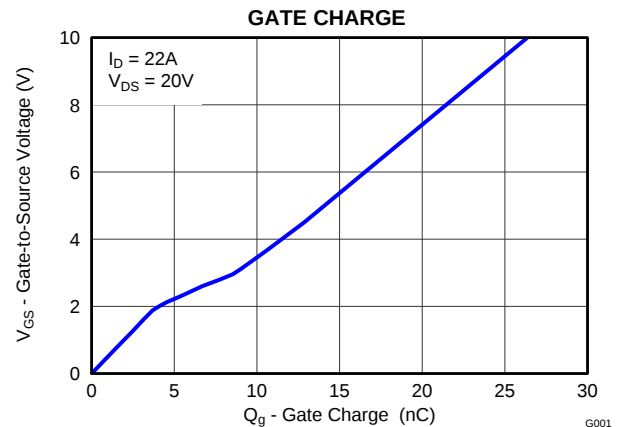
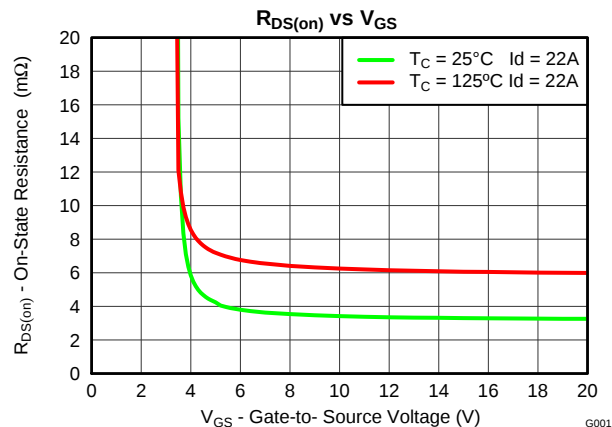
Device	Package	Media	Qty	Ship
CSD18503Q5A	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 25°C unless otherwise stated		VALUE	UNIT
V _{DS}	Drain to Source Voltage	40	V
V _{GS}	Gate to Source Voltage	±20	V
I _D	Continuous Drain Current (Package limited), T _C = 25°C	100	A
	Continuous Drain Current (Silicon limited), T _C = 25°C	145	
	Continuous Drain Current, T _A = 25°C ⁽¹⁾	19	
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	124	A
P _D	Power Dissipation ⁽¹⁾	3.1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E _{AS}	Avalanche Energy, single pulse I _D = 56A, L = 0.1mH, R _G = 25Ω	157	mJ

(1) Typical R_{θJA} = 40°C/W on a 1-inch², 2-oz. Cu pad on a 0.06-inch thick FR4 PCB.

(2) Pulse duration ≤300μs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

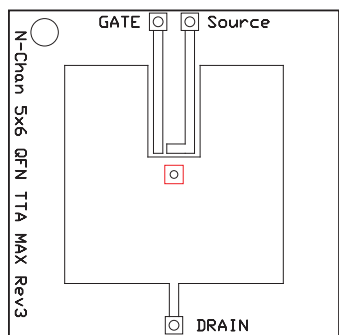
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
B _V DSS	Drain to Source Voltage	V _{GS} = 0V, I _D = 250μA	40			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 32V			1	μA
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = 20V			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.5	1.8	2.3	V
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 4.5V, I _D = 22A	4.7		6.2	mΩ
		V _{GS} = 10V, I _D = 22A	3.4		4.3	mΩ
g _{fs}	Transconductance	V _{DS} = 20V, I _D = 22A	100			S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 20V, f = 1MHz	2200		2640	pF
C _{oss}	Output Capacitance		510		612	pF
C _{rss}	Reverse Transfer Capacitance		13		16	pF
R _G	Series Gate Resistance		1.2	2.4		Ω
Q _g	Gate Charge Total (4.5V)	V _{DS} = 20V, I _D = 22A	13		16	nC
Q _g	Gate Charge Total (10V)		27		32	
Q _{gd}	Gate Charge Gate to Drain		4.3			nC
Q _{gs}	Gate Charge Gate to Source		4.5			nC
Q _{g(th)}	Gate Charge at V _{th}		3.8			nC
Q _{oss}	Output Charge	V _{DS} = 20V, V _{GS} = 0V	30			nC
t _{d(on)}	Turn On Delay Time	V _{DS} = 20V, V _{GS} = 10V, I _{DS} = 22A, R _G = 0	4.5			ns
t _r	Rise Time		8.8			ns
t _{d(off)}	Turn Off Delay Time		15			ns
t _f	Fall Time		2.6			ns
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _{SD} = 22A, V _{GS} = 0V	0.8		1	V
Q _{rr}	Reverse Recovery Charge	V _{DS} = 20V, I _F = 22A, di/dt = 300A/μs	52			nC
t _{rr}	Reverse Recovery Time		37			ns

THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

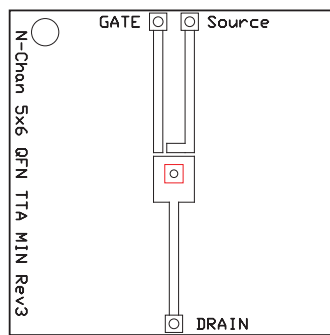
PARAMETER		MIN	TYP	MAX	UNIT
R _{θJC}	Thermal Resistance Junction to Case ⁽¹⁾			1	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			50	°C/W

- (1) R_{θJC} is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.



M0137-01

Max $R_{\theta JA} = 50^{\circ}\text{C/W}$
when mounted on
1 inch² (6.45 cm²) of 2-
oz. (0.071-mm thick)
Cu.

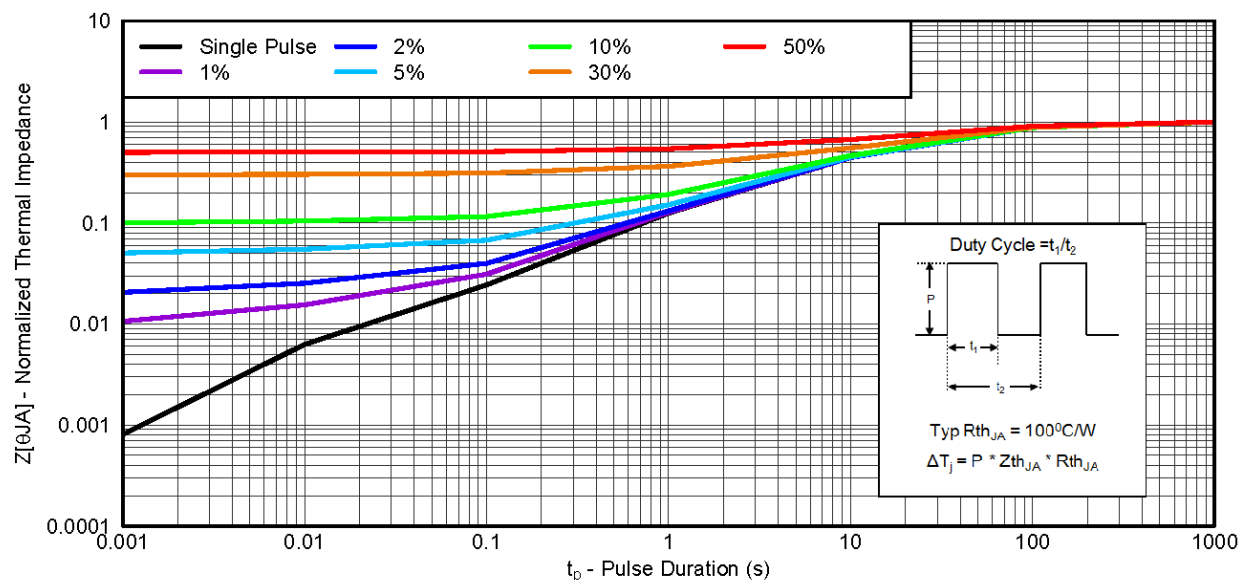


M0137-02

Max $R_{\theta JA} = 125^{\circ}\text{C/W}$
when mounted on a
minimum pad area of
2-oz. (0.071-mm thick)
Cu.

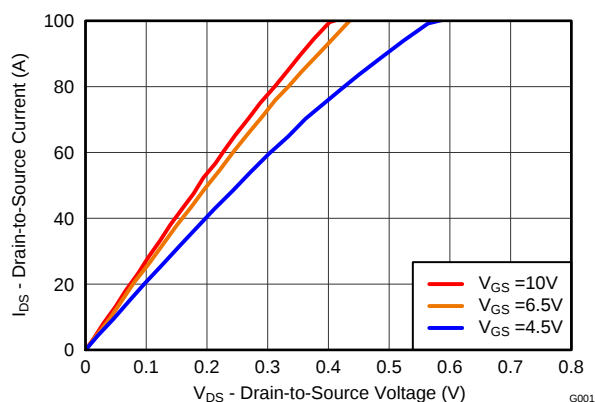
TYPICAL MOSFET CHARACTERISTICS

($T_A = 25^{\circ}\text{C}$ unless otherwise stated)



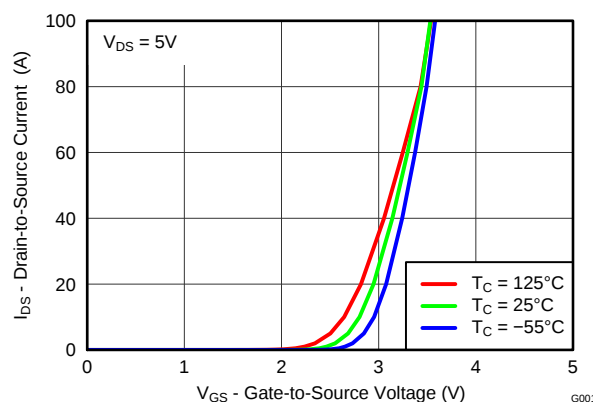
G001

Figure 2. Transient Thermal Impedance



G001

Figure 3. Saturation Characteristics



G001

Figure 4. Transfer Characteristics

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

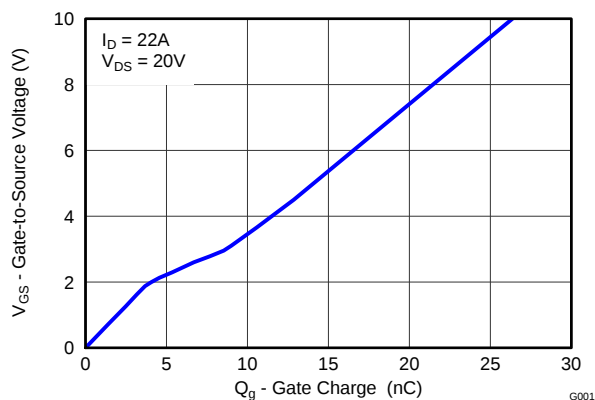


Figure 5. Gate Charge

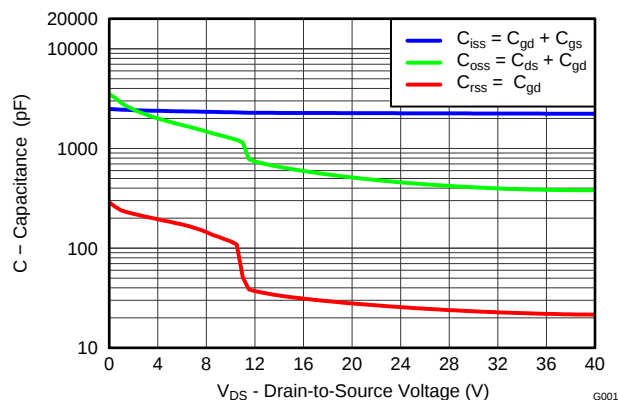


Figure 6. Capacitance

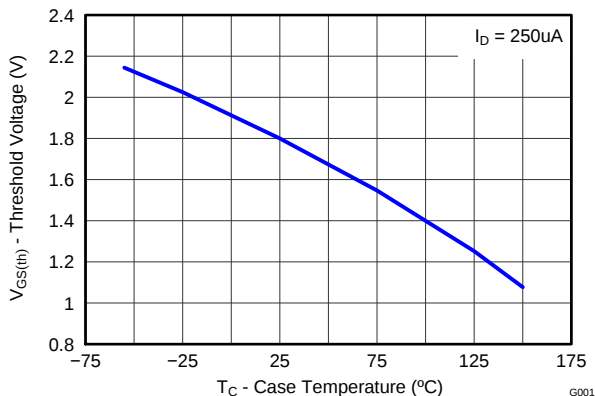


Figure 7. Threshold Voltage vs. Temperature

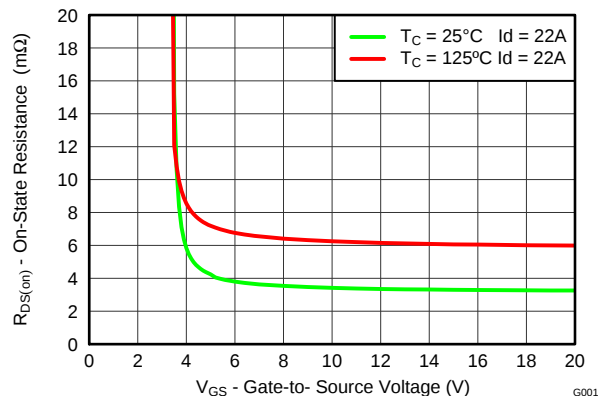


Figure 8. On-State Resistance vs. Gate-to-Source Voltage

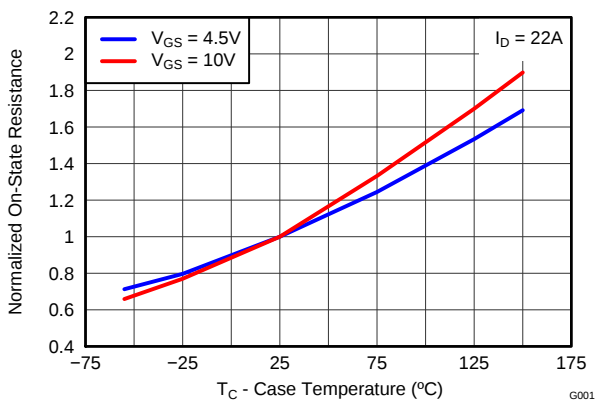


Figure 9. Normalized On-State Resistance vs. Temperature

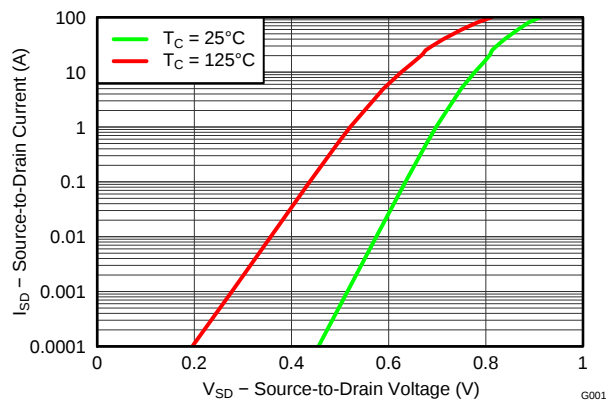


Figure 10. Typical Diode Forward Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

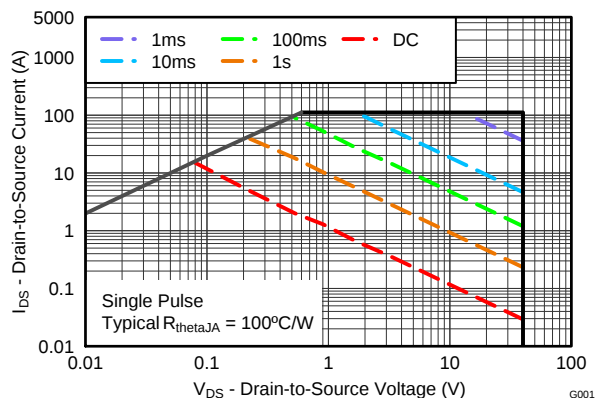


Figure 11. Maximum Safe Operating Area

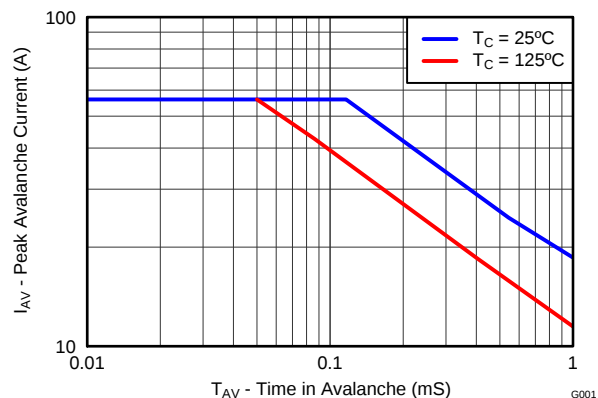


Figure 12. Single Pulse Unclamped Inductive Switching

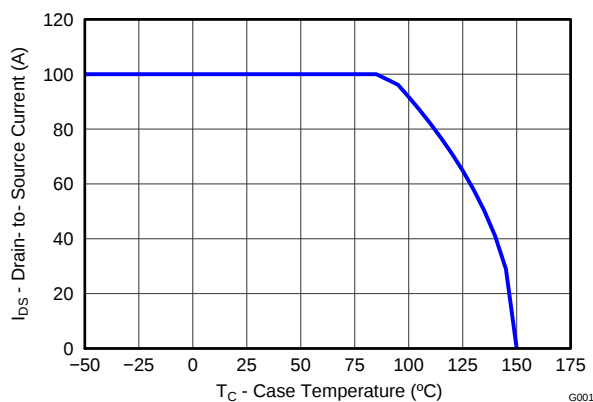
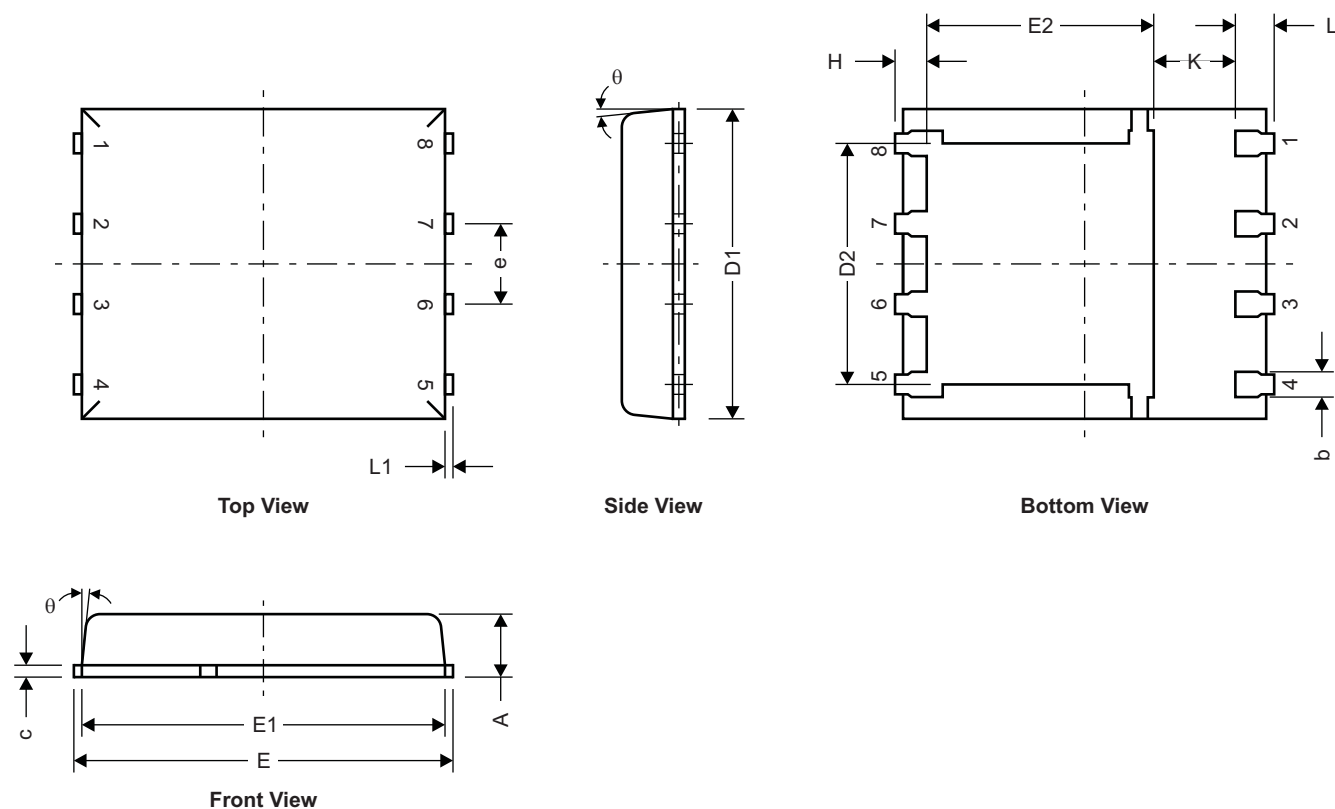


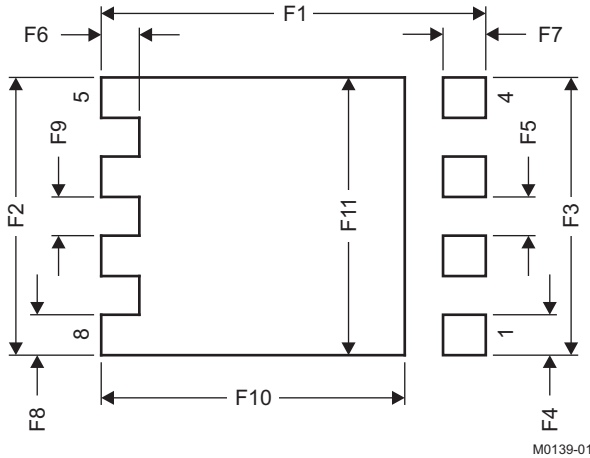
Figure 13. Maximum Drain Current vs. Temperature

MECHANICAL DATA**Q5A Package Dimensions**

M0135-01

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.41	0.51
c	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.17	1.27	1.37
H	0.41	0.56	0.71
K	1.10		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°		12°

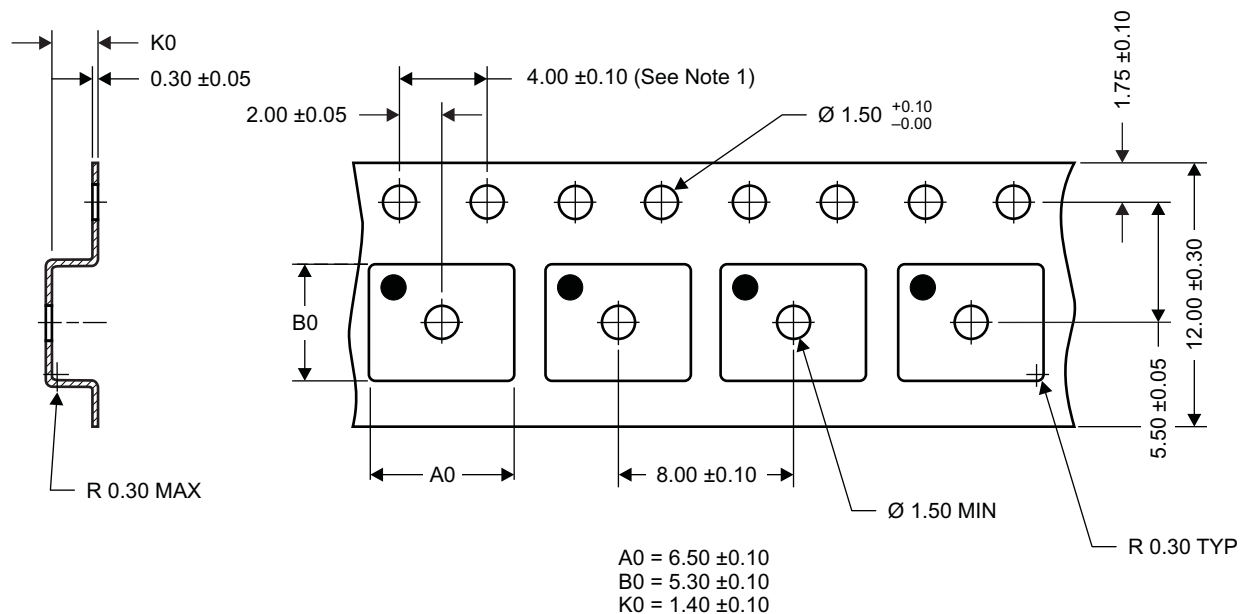
Figure 14. Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note [SLPA005 – Reducing Ringing Through PCB Layout Techniques](#).

Q5A Tape and Reel Information



Notes:

- 10-sprocket hole-pitch cumulative tolerance ± 0.2
- Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- Material: black static-dissipative polystyrene
- All dimensions are in mm (unless otherwise specified)
- A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

REVISION HISTORY

Changes from Original (June 2012) to Revision A Page

- Changed the Transconductance TYP value From: 127 S To: 100 S 2
- Changed the Turn On and Turn Off Delay Time, Rise and Fall Time Test Conditions From: $I_{DS} = 22A$, $R_G = 2\Omega$ To:
 $I_{DS} = 22A$, $R_G = 0\Omega$ 2
- Changed the Q_{rr} Reverse Recovery Charge TYP value From: 22 nC To: 52 nC 2

Changes from Revision A (October 2012) to Revision B Page

- Changed the $R_{DS(on)}$ vs V_{GS} and GATE CHARGE graphs 1
- Changed Max $R_{\theta JA} = 121^\circ C/W$ To: Max $R_{\theta JA} = 125^\circ C/W$ 3
- Changed the TYPICAL MOSFET CHARACTERISTICS section 3

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Samples (Requires Login)
CSD18503Q5A	ACTIVE	SON	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

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⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18503Q5A	SON	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD18503Q5A	SON	DQJ	8	2500	340.0	340.0	38.0

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- Техническая поддержка проекта;
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